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SUD08P06-155L-GE3

Vishay Semiconductors

MOSFET -30V 0.155ohm@-10V -8.4A P-CH

Any questions, please feel free to contact us. info@kaimte.com





P-Channel 60 V (D-S) MOSFET

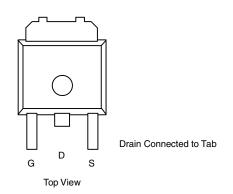
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ)		
- 60	0.155 at V _{GS} = - 10 V	- 8.4	12.5		
- 60	0.280 at V _{GS} = - 4.5 V	- 7.4	12.5		

FEATURES

- TrenchFET® Power MOSFETS
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

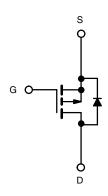






Ordering Information:

SUD08P06-155L-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Gate-Source Voltage	V_{GS}	± 20	V			
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 25 °C	I _D	- 8.2			
Continuous Brain Current (1) = 130 O)	T _C = 100 °C	טי	- 5.2			
Pulsed Drain Current	I _{DM}	- 18	A			
Continuing Source Current (Diode Conduction)	I _S	- 8.4				
Avalanche Current	I _{AS}	- 12				
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	7.2	mJ		
Maximum Power Dissipation	T _C = 25 °C	P _D 20.8 ^a		W		
Maximum Fower Dissipation	T _A = 25 °C] 'D [1.7 ^b	VV		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^b	t ≤ 10 s	B	20	25	°C/W	
Junction-to-Ambient	Steady State	R_{thJA}	62	75		
Junction-to-Case		R _{thJC}	5	6		

- a. See SOA curve for voltage derating.
- b. Surface mounted on 1" x 1" FR-4 boad.

Document Number: 62843 S13-0788-Rev. A, 15-Apr-13 For technical questions, contact: pmostechsupport@vishay.com

SUD08P06-155L-GE3

Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 60	- 60		V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1	- 2	- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = - 60 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 125 °C			- 50	μΑ	
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 150 °C			- 150		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 10			Α	
		V _{GS} = - 10 V, I _D = - 5 A		0.125	0.155		
5 : 6 h	D	V _{GS} = - 10 V, I _D = - 5 A, T _J = 125 °C			0.280		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 5 A, T _J = 150 °C			0.350	Ω	
		V _{GS} = - 4.5 V, I _D = - 2 A		0.158	0.280	1	
Forward Transconductance ^b	9 _{fs}	V _{DS} = - 15 V, I _D = - 5 A		8		S	
Dynamic		<u> </u>					
Input Capacitance	C _{iss}			450		pF	
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		65			
Reverse Transfer Capacitance	C _{rss}			40			
Total Gate Charge	Qg			12.5	19		
Gate-Source Charge	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -8.4 \text{ A}$		2.3		nC	
Gate-Drain Charge	Q _{gd}			3.2			
Gate Resistance	R_g	f = 1 MHz		8		Ω	
Turn-On Delay Time ^c	t _{d(on)}			5	10		
Rise Time ^c	t _r	$V_{DD} = -30 \text{ V}, R_{L} = 3.57 \Omega$		14	25	no	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ - 8.4 A, V_{GEN} = - 10 V, R_G = 2.5 Ω		15	25	ns	
Fall Time ^c	t _f]		7	12		
Source-Drain Diode Ratings and Cha	racteristics	(T _C = 25 °C) ^b					
Pulsed Current	I _{SM}				- 20	Α	
Forward Voltage ^b	V_{SD}	I _F = - 2 A, V _{GS} = 0 V		- 0.9	- 1.3	V	
Reverse Recovery Time	t _{rr}	L = 9 A dl/d+ 400 A/vo		50	80	ns	
Reverse Recovery Time	Q _{rr}	I _F = - 8 A, dI/dt = 100 A/μs		80	120	nC	

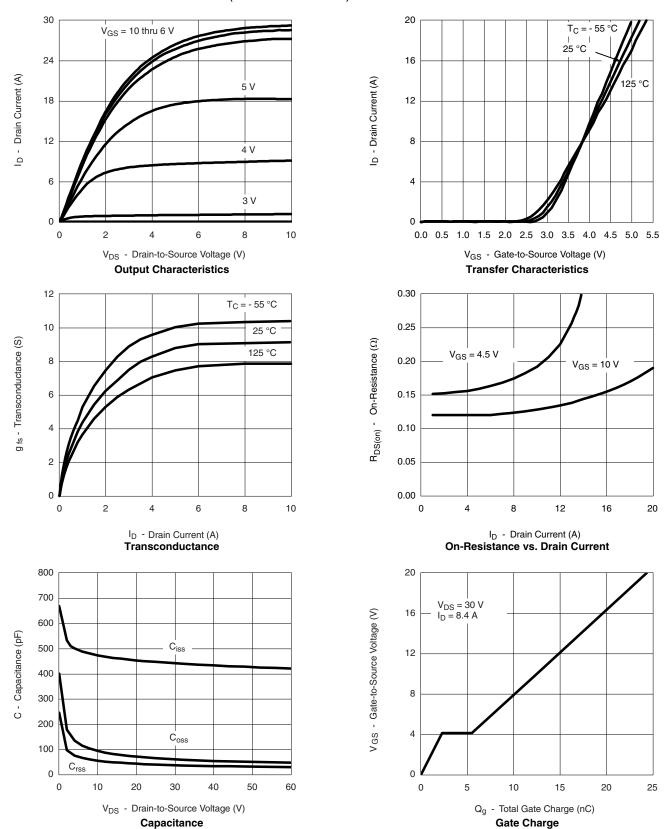
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

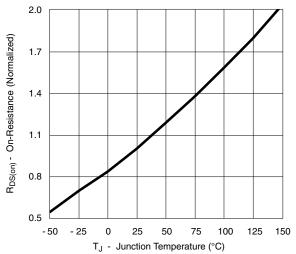


TYPICAL CHARACTERISTICS (25 °C unless noted)

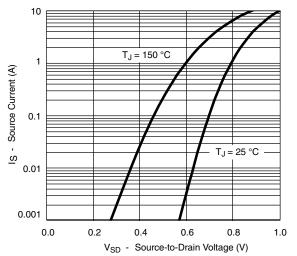


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TYPICAL CHARACTERISTICS (25 °C unless noted)

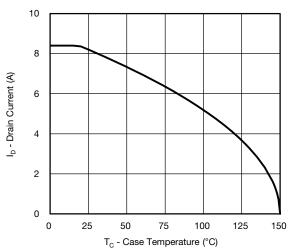


On-Resistance vs. Junction Temperature

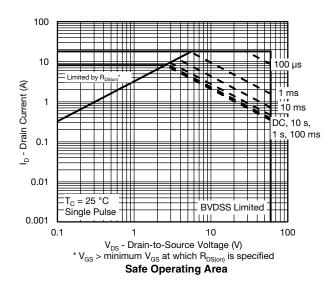


Source-Drain Diode Forward Voltage

THERMAL RATINGS

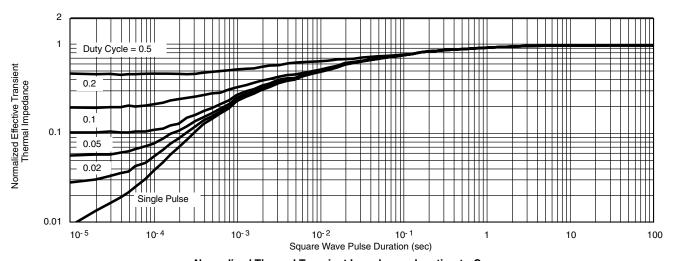


Drain Current vs. Case Temperature





THERMAL RATINGS



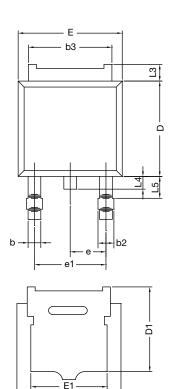
Normalized Thermal Transient Impedance, Junction-to-Case

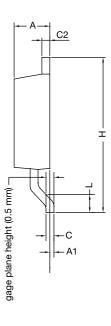
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TO-252AA Case Outline





	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	=	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC		0.090 BSC		
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T16-0236-Rev. P, 16-May-16					

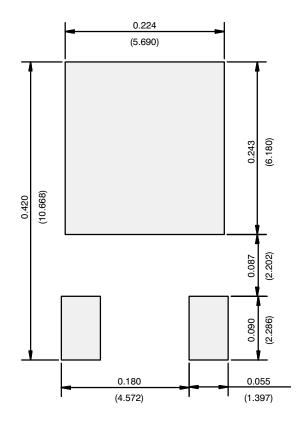
DWG: 5347

Notes

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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